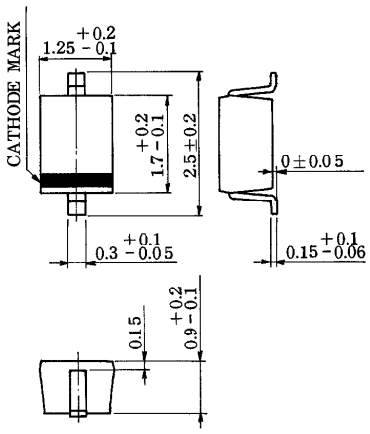
TOSHIBA DIODE SILICON EPITAXIAL SCHOTTKY BARRIER TYPE

1SS367

HIGH SPEED SWITCHING APPLICATION

Unit in mm



USC	
JEDEC	—
EIAJ	—
TOSHIBA	1-1E1A

Weight : 0.004g

- Small Package
- Low Forward Voltage : $V_F = 0.23V$ (TYP.) @$I_F = 5mA$

MAXIMUM RATINGS (Ta = 25°C)

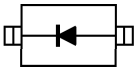
CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage	V_{RM}	15	V
Reverse Voltage	V_R	10	V
Maximum (Peak) Forward Current	I_{FM}	200	mA
Average Forward Current	I_O	100	mA
Surge Current (10ms)	I_{FSM}	1	A
Power Dissipation	P※	200	mW
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	−55~125	°C
Operating Temperature Range	T_{opr}	−40~100	°C

※ Mounted on a glass epoxy circuit board of 20×20mm Pad dimension of 4×4mm.

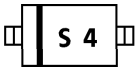
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	$V_{F(1)}$	$I_F = 1mA$	—	0.18	—	V
	$V_{F(2)}$	$I_F = 5mA$	—	0.23	0.30	
	$V_{F(3)}$	$I_F = 100mA$	—	0.35	0.50	
Reverse Current	I_R	$V_R = 10V$	—	—	20	μA
Total Capacitance	C_T	$V_R = 0$, f = 1MHz	—	20	40	pF

EQUIVALENT CIRCUIT (TOP VIEW)



MARKING



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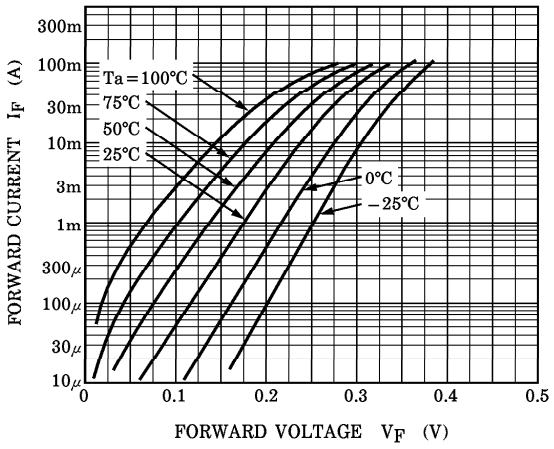
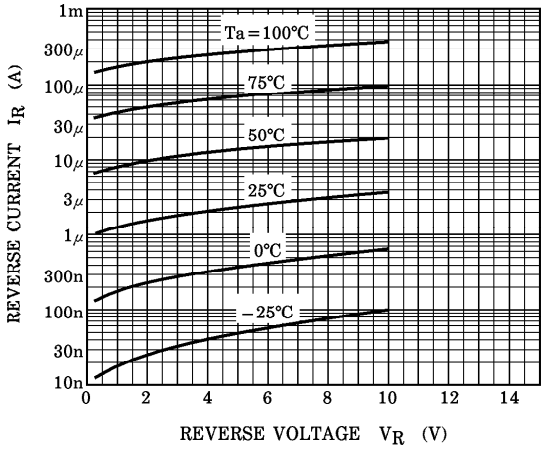
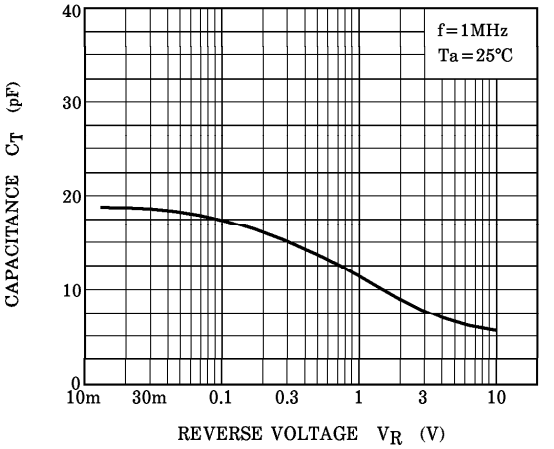
$I_F - V_F$



$I_R - V_R$



$C_T - V_R$



P – Ta